CM1485

Dual Channel EMI Filter with ESD Protection

Product Description

The CM1485 is a 2 channel pi-style EMI filter array with ESD protection, housed in a 6−lead SOT−563 package. The CM1485 has component values of 12 pF − 100 Ω − 12 pF per channel. The CM1485 has a cut−off frequency of 125 MHz and can be used in applications with data rates up to 48 Mbps. The parts include ESD diodes on every pin, which provide a very high level of protection for sensitive electronic components that may be subjected to electrostatic discharge (ESD). The ESD protection diodes safely dissipate ESD strikes of ±15 kV, well beyond the maximum requirement of the IEC61000−4−2 international standard. Using the MIL−STD−883 (Method 3015) specification for Human Body Model (HBM) ESD, the pins are protected for contact discharges at greater than ±30 kV.

This device is particularly well−suited for portable electronics (e.g. wireless handsets, PDAs, notebook computers) because of its small package and easy-to-use pin assignments. In particular, the CM1485 is ideal for EMI filtering and protecting data and control lines for the I/O data ports, LCD display and camera interface in mobile handsets.

The CM1485 is housed in a small, 6−lead SOT−563 package and is available with lead−free finishing.

Features

- Two Channels of EMI Filtering with Integrated ESD Protection
- Pi−Style EMI Filters in a Capacitor−Resistor−Capacitor (C−R−C) Network
- ±15 kV ESD Protection on Each Channel (IEC 61000−4−2 Level 4, Contact Discharge)
- ±30 kV ESD Protection on Each Channel (HBM)
- Greater than 30 dB Attenuation (Typical) at 1 GHz
- 6−lead SOT−563 Package
- These Devices are Pb−Free and are RoHS Compliant

Applications

- LCD and Camera Data Lines in Mobile Handsets
- I/O Port Protection for Mobile Handsets, Notebook Computers, PDAs, etc.
- EMI Filtering for Data Ports in Cell Phones, PDAs or Notebook Computers
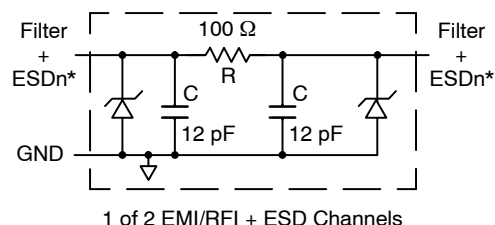- Wireless Handsets
- Handheld PCs/PDAs
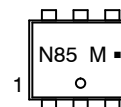- LCD and Camera Modules

ON Semiconductor®

http://onsemi.com

SOT−563
SE SUFFIX
CASE 463A

ELECTRICAL SCHEMATIC

1 of 2 EMI/RFI + ESD Channels

* See Package/Pinout Diagrams for expanded pin information.

MARKING DIAGRAM

N85 = CM1485−02SE
M = Month Code
▪ = Pb−Free Package

ORDERING INFORMATION

| Device	Package	Shipping[†]
CM1485−02SE	SOT−563 (Pb−Free)	5000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Table 1. PIN DESCRIPTIONS

6−Lead SOT−563 Package		
Pin	**Name**	**Description**
1	FILTER1	Filter + ESD Channel 1
2	GND	Ground (Note 1)
3	FILTER1	Filter + ESD Channel 1
4	FILTER2	Filter + ESD Channel 2
5	GND	Ground (Note 1)
6	FILTER2	Filter + ESD Channel 2

1. Pin 2 and Pin 5 must be well grounded at the same time.

PACKAGE / PINOUT DIAGRAMS

Top View

CH1 — 1   5 — CH2
GND — 2 N85 5 — GND
CH1 — 3   4 — CH2

6−Lead SOT−563
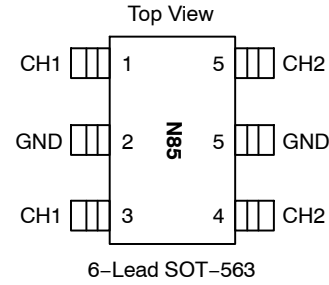
SPECIFICATIONS

Table 2. ABSOLUTE MAXIMUM RATINGS

Parameter	Rating	Units
Storage Temperature Range	−65 to +150	°C
DC Power per Resistor	100	mW
DC Package Power Rating	0.15	W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Table 3. STANDARD OPERATING CONDITIONS

Parameter	Rating	Units
Operating Temperature Range	−40 to +85	°C

Table 4. ELECTRICAL OPERATING CHARACTERISTICS (Note 1)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
R	Resistance		90	100	110	Ω
C_{TOTAL}	Total Channel Capacitance	At 2.5 V DC Reverse Bias, 1 MHz, 30 mV AC	19.2	24.0	28.8	pF
I_{LEAK}	Diode Leakage Current (Reverse Bias)	V_{DIODE} = +3.0 V			1.0	μA
V_{BR}	Breakdown Voltage Positive Clamp	I_{LOAD} = 1 mA	6.0	7.0		V
V_{ESD}	In−system ESD Withstand Voltage a) Human Body Model, MIL−STD−883, Method 3015 b) Contact Discharge per IEC 61000−4−2 Level 4	(Note 2)	±30 ±15			kV
R_{DYN}	Dynamic Resistance Positive Negative			2.3 0.9		Ω
f_C	Cut−off Frequency Z_{SOURCE} = 50 Ω, Z_{LOAD} = 50 Ω			125		MHz
A_{1GHz}	Absolute Attenuation @ 1 GHz from 0 dB Level	Z_{SOURCE} = 50 Ω, Z_{LOAD} = 50 Ω, DC Bias = 0 V (Notes 1 and 3)		35		dB
$A_{800MHz − 6GHz}$	Absolute Attenuation @ 800 MHz to 1 GHz from 0 dB Level	Z_{SOURCE} = 50 Ω, Z_{LOAD} = 50 Ω, DC Bias = 0 V (Notes 1 and 3)		30		dB

1. T_A = 25°C unless otherwise specified.
2. ESD applied to input and output pins with respect to GND, one at a time.
3. Attenuation / RF curves characterized by a network analyzer using microprobes.

PERFORMANCE INFORMATION

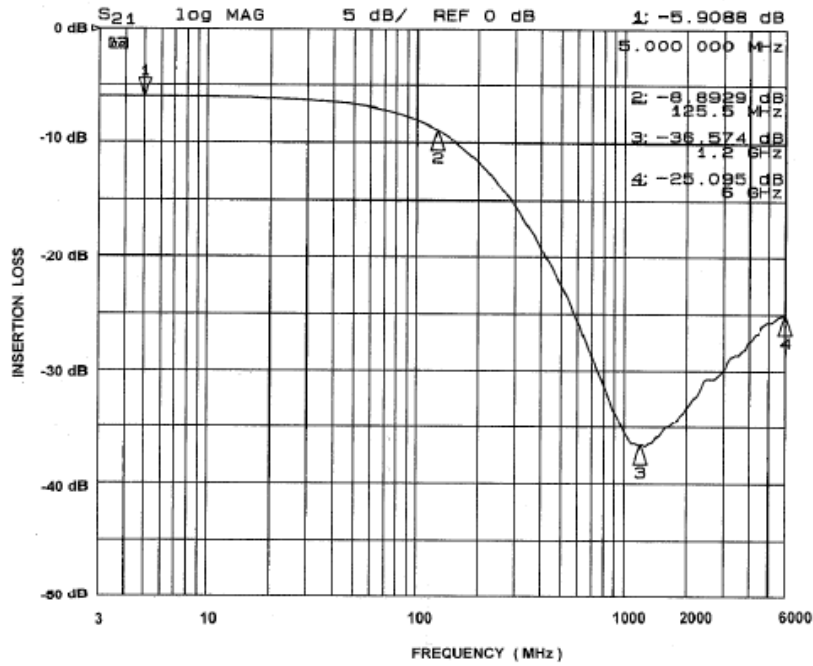**Typical Filter Performance (T$_A$ = 25°C, DC Bias = 0 V, 50 Ω Environment)**

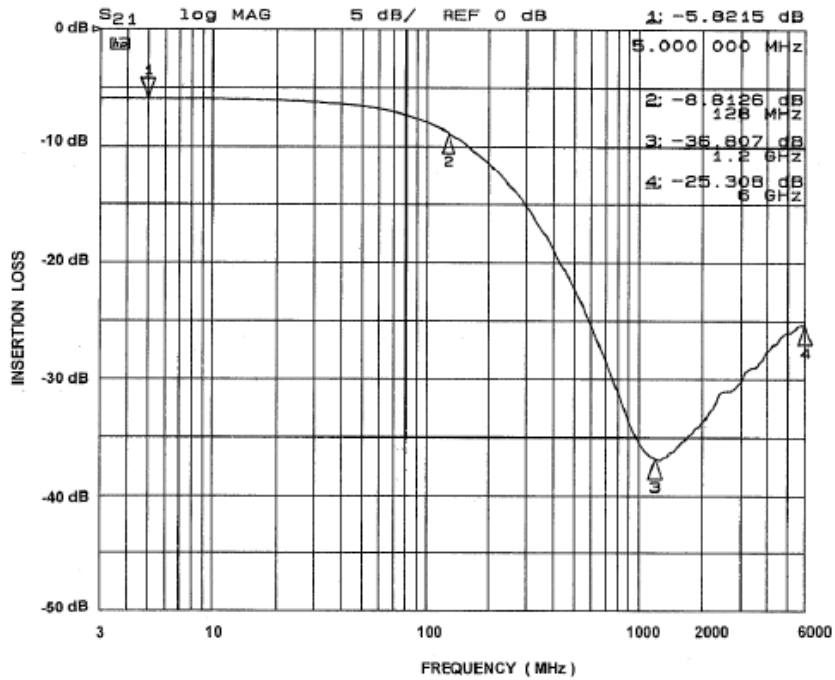**Figure 1. Insertion Loss vs. Frequency (FILTER1 Input to GND)**

Figure 2. Insertion Loss vs. Frequency (FILTER2 Input to GND)
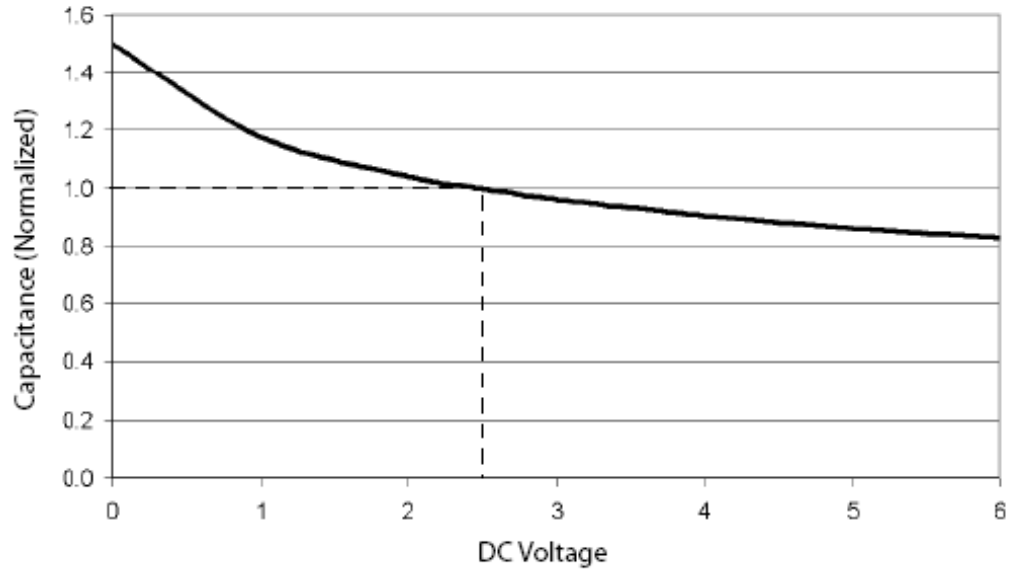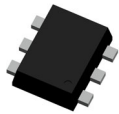
PERFORMANCE INFORMATION (Cont'd)

Figure 3. Filter Capacitance vs. Input Voltage
(normalized to capacitance at 2.5 V DC and 25°C)

SOT−563−6 1.60x1.20x0.55, 0.50P
CASE 463A
ISSUE J

DATE 15 FEB 2024

NOTES:
1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

PIN 1 REFERENCE

⊕ 0.08 Ⓜ A B

TOP VIEW

SIDE VIEW
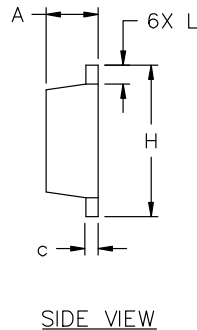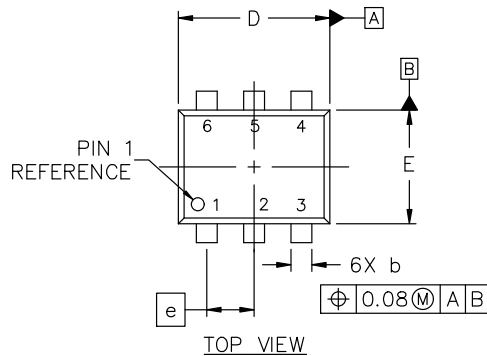
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.10	0.20	0.30

RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

GENERIC MARKING DIAGRAM*

XXM■
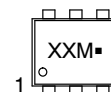
XX = Specific Device Code
M = Month Code
■ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT−563−6 1.60x1.20x0.55, 0.50P	PAGE 1 OF 1

ADDITIONAL INFORMATION

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